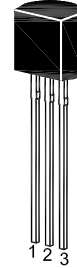


2N3704

NPN Silicon Epitaxial Planar Transistor

for general purpose applications.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Base 3. Collector
TO-92 Plastic Package

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	50	V
Collector Emitter Voltage	V_{CEO}	30	V
Emitter Base Voltage	V_{EBO}	5	V
Collector Current	I_C	600	mA
Power Dissipation	P_{tot}	625	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
DC Current Gain at $V_{CE} = 2\text{ V}$, $I_C = 50\text{ mA}$	h_{FE}	100	300	-
Collector Base Cutoff Current at $V_{CB} = 20\text{ V}$	I_{CBO}	-	100	nA
Emitter Base Cutoff Current at $V_{EB} = 3\text{ V}$	I_{EBO}	-	100	nA
Collector Base Breakdown Voltage at $I_C = 100\text{ }\mu\text{A}$	$V_{(BR)CBO}$	50	-	V
Collector Emitter Breakdown Voltage at $I_C = 10\text{ mA}$	$V_{(BR)CEO}$	30	-	V
Emitter Base Breakdown Voltage at $I_E = 100\text{ }\mu\text{A}$	$V_{(BR)EBO}$	5	-	V
Collector Emitter Saturation Voltage at $I_C = 100\text{ mA}$, $I_B = 5\text{ mA}$	$V_{CE(sat)}$	-	0.6	V
Base Emitter On Voltage at $V_{CE} = 2\text{ V}$, $I_C = 100\text{ mA}$	$V_{BE(on)}$	0.5	1	V
Gain Bandwidth Product at $V_{CE} = 2\text{ V}$, $I_C = 50\text{ mA}$, $f = 20\text{ MHz}$	f_T	100	-	MHz
Collector Output Capacitance at $V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{ob}	-	12	pF